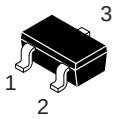
N-Channel JFET

15 V, 10 to 24 mA, 50 mS, CP

2SK932



1: Source
2: Drain
3: Gate

SC−59 / CP3
CASE 318BJ

Applications

- AM Tuner RF Amplification, Low Noise Amplifier

Features

- Adoption of FBET Process
- Large | yfs |
- Small Ciss
- Ultralow Noise Figure
- Ultrasmall−sized Package Permitting 2SK932−applied Sets to be Made Smaller and Slimer
- These are Pb−Free Devices

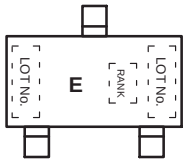
Specifications

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

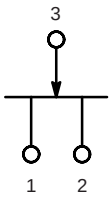
Parameter	Symbol	Conditions	Ratings	Unit
Drain−to−Source Voltage	V_{DSX}		15	V
Gate−to−Drain Voltage	V_{GDS}		−15	V
Gate Current	I_G		10	mA
Drain Current	I_D		50	mA
Allowable Power Dissipation	P_D		200	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

MARKING DIAGRAM



ELECTRICAL CONNECTION



ORDERING INFORMATION

Device	Package	Shipping†
2SK932−23−TB−E	CP (Pb−Free)	3,000 / Tape & Reel
2SK932−24−TB−E	CP (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Parameter	Symbol	Conditions	Ratings			Unit
			Min	Typ	Max	
Gate−to−Drain Breakdown Voltage	$V_{(BR)GDS}$	I_G = −10 μA, V_{DS} = 0 V	−15	−	−	V
Gate−to−Source Leakage Current	I_{GSS}					

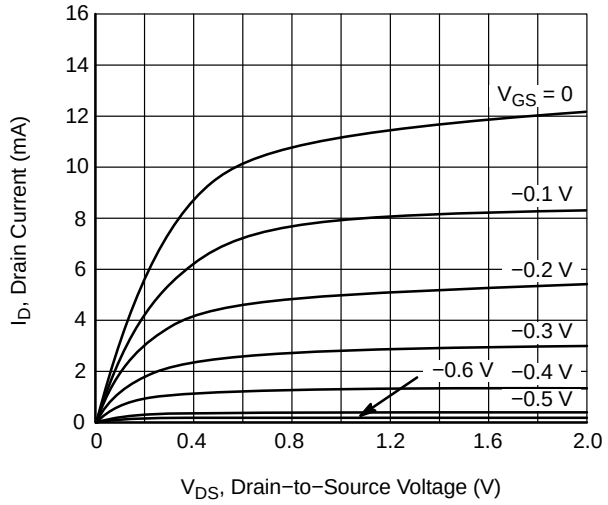


Figure 1. $I_D - V_{DS}$

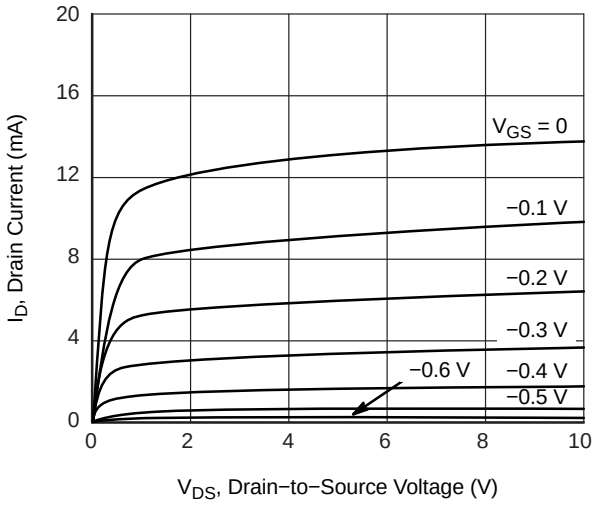


Figure 2. $I_D - V_{DS}$

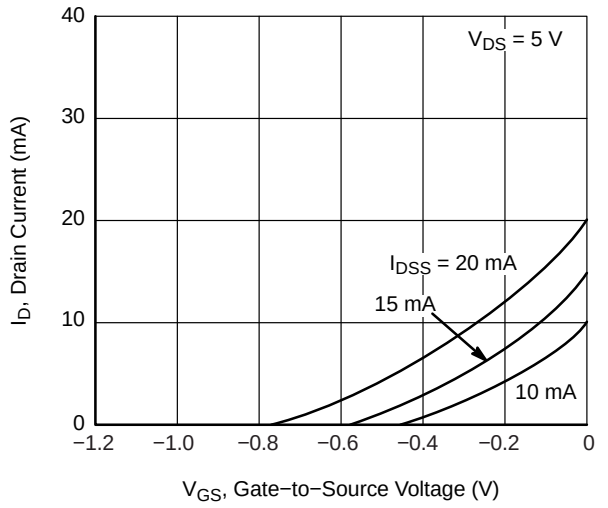


Figure 3. $I_D - V_{GS}$

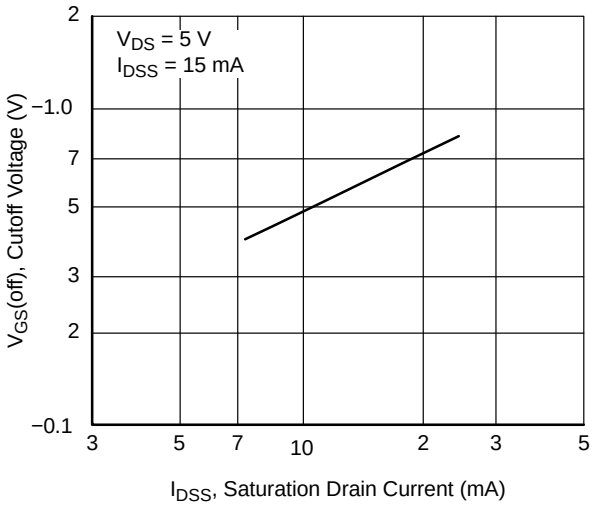


Figure 4. V_{GS}(off) − I_{DSS}

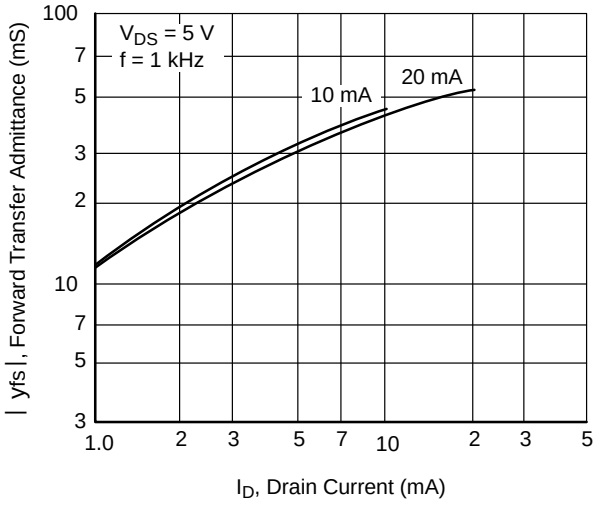


Figure 5. | yfs | − I_D

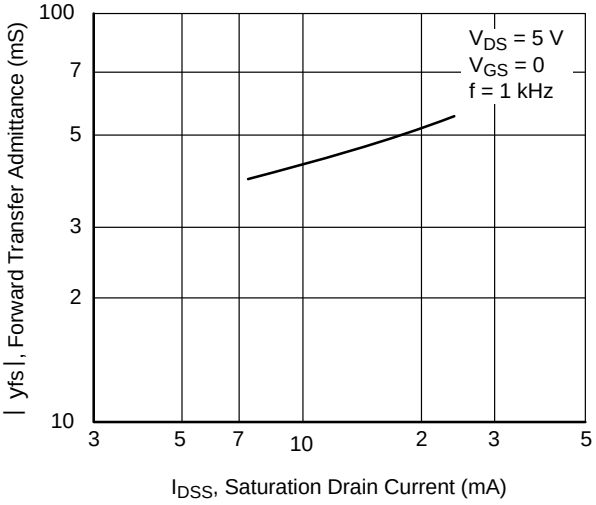
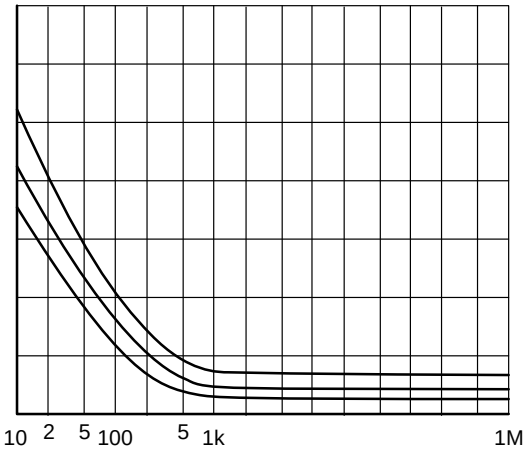
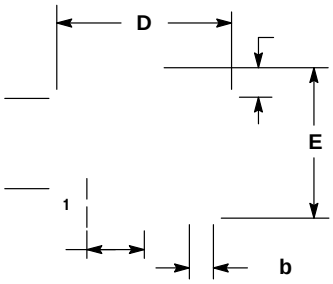


Figure 6. | yfs | − I_{DSS}


10
2
5
100
5
1k
1M

SC−59 / CP3

1



DIM	MILLIMETERS MIN	MAX
A